



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Shigeharu MONOE et al.

Serial No. 10/777,117

Filed: February 13, 2004

For: MANUFACTURING METHOD FOR
SEMICONDUCTOR DEVICE

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Examiner: Michael Manh Trinh

Group Art Unit: 2822

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure as set forth in 37 C.F.R. §1.56, Applicants hereby submit the following information in conformance with 37 C.F.R. §§ 1.97 and 1.98. Pursuant to 37 C.F.R. § 1.98, a copy of each of the documents cited is enclosed.

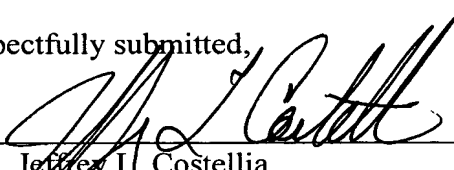
The documents are being submitted within three (3) months of the filing of this application or entry into the national stage of this application, or before the first Office Action on the merits, whichever is later, therefore no fee or certification is required under 37 C.F.R. § 1.97(b).

It is requested that the accompanying PTO-1449 be considered and made of record in the above-identified application. To assist the Examiner, the documents are listed on the attached form PTO-1449. It is respectfully requested that an Examiner initial a copy of this form be returned to the undersigned.

The Commissioner is hereby authorized to charge any fees connected with this filing which may be required now, or credit any overpayment to Deposit Account No. 19-2380.

Respectfully submitted,

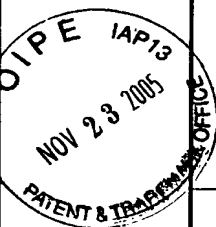
By:



Jeffrey L. Costellia
Registration No. 35,483

NIXON PEABODY LLP
Suite 900
401 9th Street, N.W.
Washington, DC 20004-2128
Telephone: (202) 585-8000

Dated: November 23, 2005



Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known		
				Application Number	10/777,117	
Sheet		1	of	1	Filing Date	February 13, 2004
					First Named Inventor	Shigeharu MONOE et al.
					Art Unit	2871
					Examiner Name	Michael Manh Trinh
					Attorney Docket Number	740756-2714

U.S. PATENT DOCUMENTS					
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
		US-6,933,184 B2	08/23/2005	Arao et al.	
		US-6,872,604 B2	03/29/2005	Yamazaki et al.	
		US-6,706,544 B2	03/16/2004	Yamazaki et al.	
		US-6,596,571 B2	07/22/2003	Arao et al.	
		US-2004/0140472 A1	07/22/2004	Fujimoto et al.	
		US-2003/0100151 A1	05/29/2003	Okamoto	
		US-2003/0062524 A1	04/03/2003	Kimura	
		US-2003/0020118 A1	01/30/2003	Kajiwara et al.	
		US-2002/0163049 A1	11/07/2002	Yamazaki et al.	
		US-2001/0048408 A1	12/06/2001	Koyama et al.	
		US-2005/0181610 A1	08/18/2005	Sasagawa et al.	
		US-2004/0209409 A1	10/21/2004	Monoe et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		OHGATA, K. et al., "A New Dopant Activation Technique for Poly-Si TFTs with a Self-Aligned Gate-Overlapped LDD Structure", <u>IEDM: Technical Digest of International Electron Devices Meeting</u> , (12/10/2000), pp. 205-208, San Francisco, USA	
		MISHIMA, Y. et al., "Improved Lifetime of Poly-Si TFTS with a Self-Aligned Gate-Overlapped LDD Structure", <u>IEEE Transactions on Electron Devices</u> , (06/2002), Vol. 49, No. 6, pp. 981-985	

Examiner Signature	Date Considered
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.